



SOT-23 Plastic-Encapsulate Transistors

MMBTA92 TRANSISTOR (PNP)

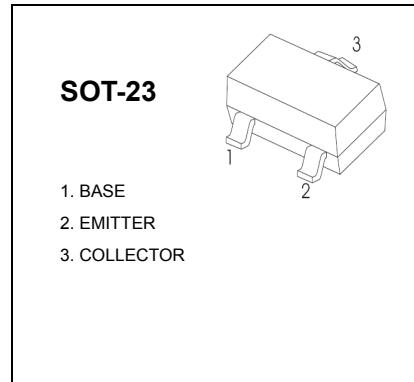
FEATURES

High voltage transistor

MARKING:2D

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|-----------|---|---------|---------------------------|
| V_{CBO} | Collector-Base Voltage | -300 | V |
| V_{CEO} | Collector-Emitter Voltage | -300 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_c | Collector Current -Continuous | -200 | mA |
| I_{CM} | Collector Current -Pulsed | -500 | mA |
| P_c | Collector Power Dissipation | 300 | mW |
| T_j | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -55-150 | $^\circ\text{C}$ |
| R_{eJA} | Thermal Resistance from Junction to Ambient | 417 | $^\circ\text{C}/\text{W}$ |

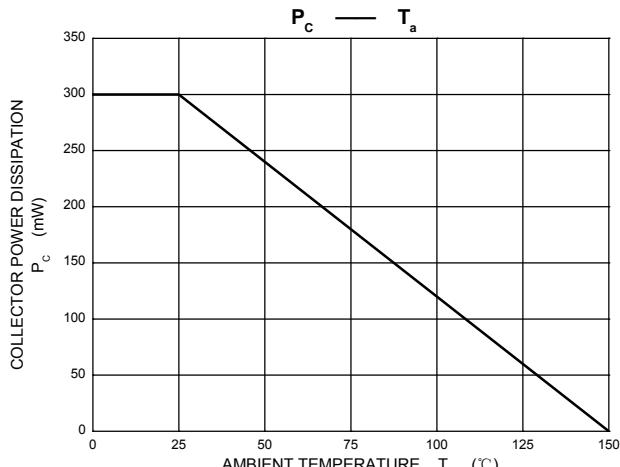
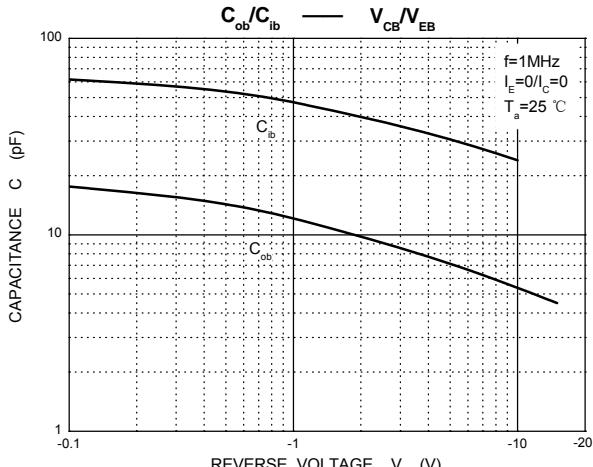
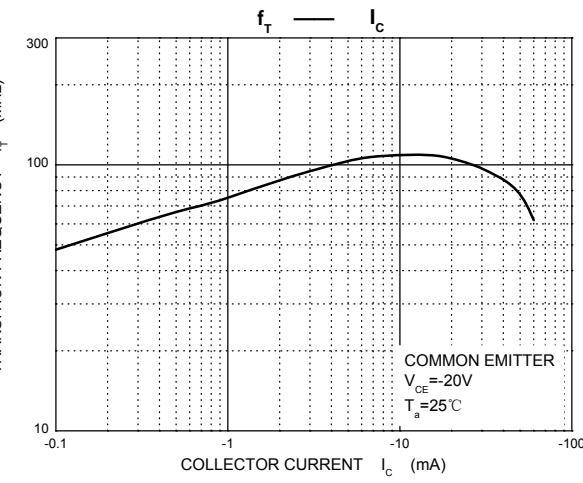
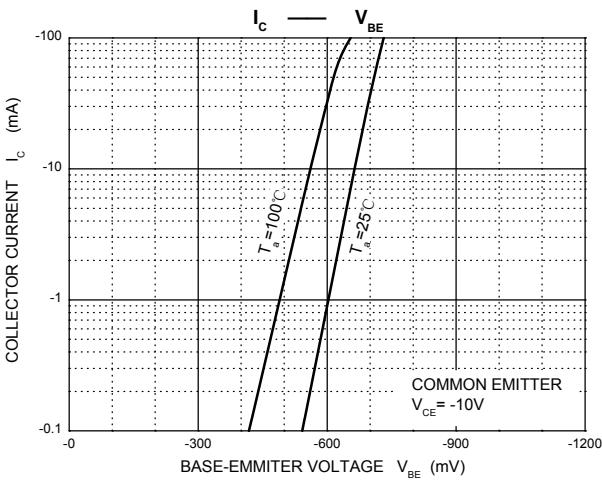
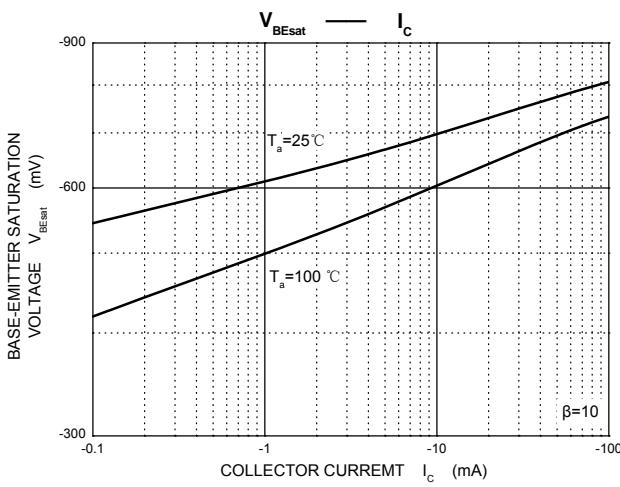
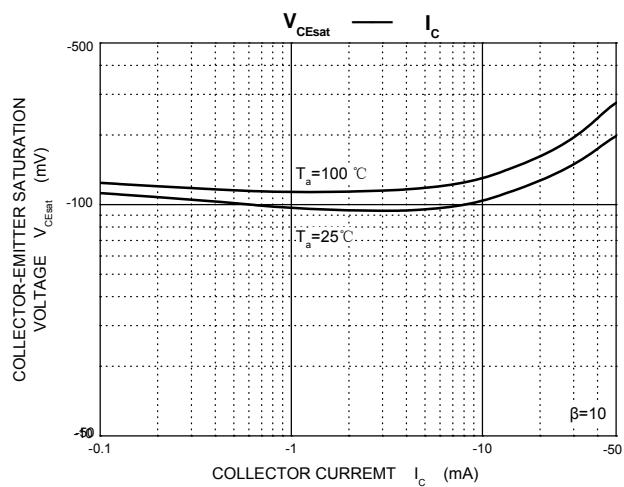
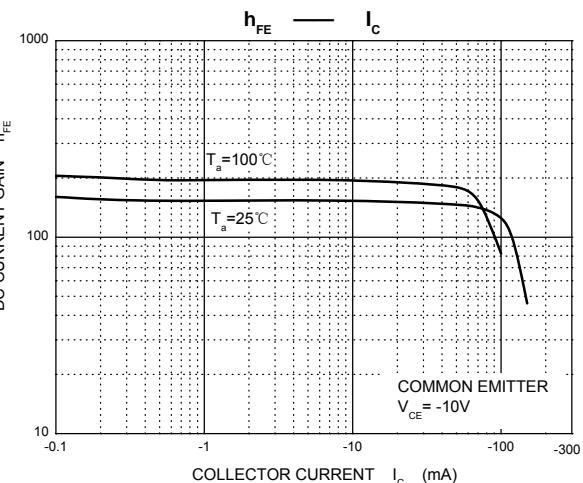
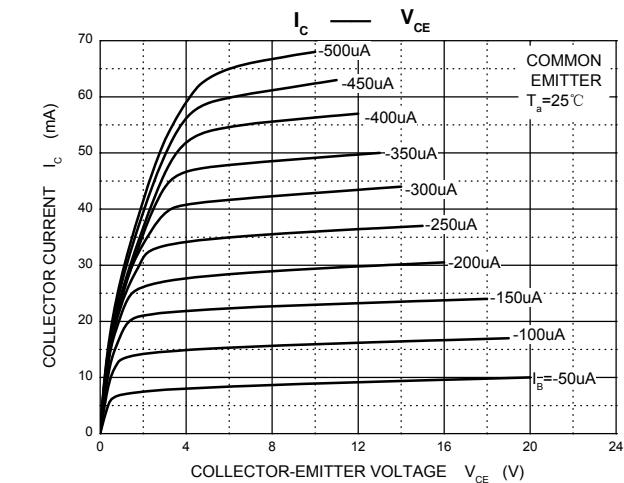


ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Max | Unit |
|--------------------------------------|---------------|--|------|-------|---------------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C = -100\mu\text{A}, I_E = 0$ | -300 | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C = -1\text{mA}, I_B = 0$ | -300 | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E = -100\mu\text{A}, I_C = 0$ | -5 | | V |
| Collector cut-off current | I_{CBO} | $V_{CB} = -200\text{V}, I_E = 0$ | | -0.25 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -5\text{V}, I_C = 0$ | | -0.1 | μA |
| DC current gain | $h_{FE(1)}$ | $V_{CE} = -10\text{V}, I_C = -1\text{mA}$ | 60 | | |
| | $h_{FE(2)}$ | $V_{CE} = -10\text{V}, I_C = -10\text{mA}$ | 100 | 200 | |
| | $h_{FE(3)}$ | $V_{CE} = -10\text{V}, I_C = -30\text{mA}$ | 60 | | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -20\text{mA}, I_B = -2\text{mA}$ | | -0.2 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | $I_C = -20\text{mA}, I_B = -2\text{mA}$ | | -0.9 | V |
| Transition frequency | f_T | $V_{CE} = -20\text{V}, I_C = -10\text{mA}$ $f = 30\text{MHz}$ | 50 | | MHz |

Typical Characteristics

MMBT A92



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